Vacancy Ordering as a Driving Factor for Structural Changes in Ternary Germanides: The New $R_2Zn_{1-x}Ge_6$ Series of Polar Intermetallics $(R = \text{Rare-Earth Metal})$

Pavlo Solokha,^{*,†} Serena De Negri,[†] Davide M. Proserpio,^{‡,§} Vladislav A. Blatov,[§] and Adriana Saccone[†]

[†]Dipartimento di [Ch](#page-12-0)imica e Chimica Industriale, Università di Genova, Via Dodecaneso 31, 16146 Genova, Italy ‡ Dipartimento di Chimica, Universitàdegli Studi di Milano, Via Golgi 19, 20133 Milano, Italy

§ Samara Center for Theoretical Materials Science (SCTMS), Samara State University, Ac. Pavlov Street 1 Samara 443011, Russia

S Supporting Information

[AB](#page-12-0)STRACT: [Synthesis and](#page-12-0) structural characterization of the new compounds $R_2Zn_{1-x}Ge_6$ (R = La–Nd, Sm, Gd–Ho) is reported. A structural change was revealed along this series by careful analysis of single-crystal X-ray diffraction data. For light rare earths up to Tb the orthorhombic δ S72-Ce₂(Ga_{0.1}Ge_{0.9})₇ model was established; instead, the Dy compound represents a new structure type $(P_1/m,$ mP34, Z = 4, a = 7.9613(3) Å, b = 8.2480(4) Å, c = 10.5309(5) Å, β = 100.861(1)°) being a superstructure of the $mS36$ -La₂AlGe₆ prototype. The established structural models support the increase of Zn deficiency along the series, suggested by microprobe analysis, and its key role in governing structural changes. The vacancy ordering criterion was applied as a successful approach to find a general scheme including the structures of the $~\sim R_2MGe_6$ compounds known up to now ($R =$ rare-earth metal, $M =$ transition metal, Mg, Al, Ga) and highlighting the subtle structural differences within this family. According to this

scheme, these structures are obtained from a common aristotype (oS20-SmNiGe3) via symmetry reduction based on group– subgroup relations accompanied by ordering of vacancies. This approach was optimized with the help of the ToposPro software and extended to the R₂Zn₃Ge₆ series, enriched with new members (R = Sm, Gd–Ho) during this work. Electronic structure calculations on La_2ZnGe_6 confirm the presence of infinite covalent germanium zigzag chains and three-bonded corrugated layers connected via Zn atoms to form a polyanionic network stabilized by La atoms.

1. INTRODUCTION

Rare-earth-based binary and ternary germanides form a group of polar intermetallics extensively studied with respect to crystal structure, chemical bonding, and physical properties.^{1−6} These compounds show a great crystallographic variety, including defective structures,^{1,4} superstructures,^{3,4} and [mod](#page-12-0)ulated structures.^{5,6} From the point of view of chemical bonding various characteristic [Ge](#page-12-0)-based covalent fr[agm](#page-12-0)ents exist in these compoun[ds,](#page-12-0) including dumbbells, $7,8$ 2D motifs, $9,10$ and 3D more complex fragments, $9,11$ whose occurrence depends on the Ge concentration. Interesting phys[ica](#page-12-0)l properties, [suc](#page-12-0)h as giant magnetocaloric effect, 12 [sup](#page-12-0)erconductivity, 13 anomalous thermal expansion,⁶ and others, were also discovered in rare-earth germanides.

Investigatio[ns](#page-12-0) on series of these compounds along the whole lanthanide (R) family^{1,14} proved that their existence and structure are influenced by the nature of R, and for this reason they are good candid[ates](#page-12-0) for studies of structure/bonding/ properties relations. The role of the third component (M) is also of great interest for ternary R−M−Ge compounds.

During our recent investigation of the La−Mg−Ge phase relations the $La₂MgGe₆$ compound was found, and its structure $(\rho$ S72-Ce₂(Ga_{0.1}Ge_{0.9})₇) was established.⁴ This compound, which does not form for rare-earth metals other than lanthanum, is a member of the numerous family of R_2MG_6 phases ($R =$ rare-earth metal; $M =$ transition or main group metal) whose occurrence and crystal structures are summarized in Table 1. The metals M involved in the formation of these compounds range from the 2nd to the 13th group of the periodic [ta](#page-1-0)ble, including many transition metals.

All ∼R₂MGe₆ compounds fall into orthorhombic or monoclinic crystal families and are reported to belong to one of the following isostructural series: (a) δ S18-Ce₂CuGe₆, space group Amm2 (No. 38); (b) $oS72-Ce_2(Ga_{0.1}Ge_{0.9})_7$, space group Cmce (No. 64); (c) mS36-La₂AlGe₆, space group C2/m (No. 12). The metrics of the two orthorhombic models are related: the unit cell of the latter is four times bigger than that of the former. Nevertheless, the correctness of the oS18 model is suspicious for two reasons.

(1) This model was always deduced from X-ray powder diffraction patterns, which are not sensitive to small structural differences. In fact, the crystal structures of $(La/Dy/Yb)_2PdGe_6$ and $(La/Dy)_2PtGe_6$, previously

Received: December 21, 2014 Published: February 10, 2015

Group M														R= Y La Ce Pr Nd Sm Eu Gd Tb Dy Ho Er Tm Yb Lu			Ref.
2	Mg																$\overline{4}$
9	Co	⊠							⊠	⊠	⊠	⊠	⊠	⊠		⊠	16,17
10	Ni	⊠		×	⊠	⊠	⊠		⊠	⊠	⊠	⊠	×	⊠	⊠	⊠	16, 17
	Pd	⊠	⊠	⊠	⊠	⊠	⊠	×	⊠	⊠	⊠	⊠	⊠	×	⊠	⊠	16, 17
																	18, 19
	Pt	⊠	⊠	⊠	⊠	⊠	⊠	⊠	⊠	⊠	⊠	⊠	⊠	⊠	\boxtimes	区	16, 17
																	18
	Cu	⊠	⊠	⊠	⊠	⊠	⊠		⊠	⊠	⊠	⊠	⊠	⊠	⊠		16, 17
11	Ag		⊠	⊠	⊠	⊠	⊠		⊠								16, 17
	Au		⊠	⊠	⊠	⊠	⊠		⊠	⊠	⊠						16, 17
12	Zn																this work
13	A1		◇	◈	◈	◈	◈		◈	◈	◈						16, 17
	Ga	◈															16, 20

Table 1. Structure Types of R−M−Ge Compounds of \sim 2:1:6 Stoichiometry (R = rare-earth metal; M = metal)^a

^aA blank cell means that an alloy of this composition was not investigated.

reported as $oS18-Ce_2CuGe_6$, were subsequently reinterpreted as $oS72-Ce_2(Ga_{0.1}Ge_{0.9})_7$ after single-crystal X-ray diffraction analysis.^{18,19}

(2) This model does not agree with the symmetry principle.¹⁵ Accor[din](#page-12-0)[g](#page-13-0) to that, atoms of the same kind have the tendency to occupy the minimal number of equivale[nt](#page-12-0) positions in a crystal, a condition not satisfied by Ge atoms in the oS18 model.

The two models $oS72$ and $mS36$ are also intimately related. In fact, they can be described as belonging to a homological series constructed by linear intergrowth of inhomogeneous segments of the defective BaAl₄, AlB₂, and α -Po structure types.^{20,21} An alternative description was given by Grin,²² based on only two types of segments, AlB_2 and defective CeRe₄Si₂.

The compositions of many of the above-mentioned R−M− Ge phases are not exactly coincident with the 2:1:6 stoichiometry, being more Ge or M rich. It is the case of two prototypes: in $Ce_2(Ga_{0.1}Ge_{0.9})_7$ a statistical mixture of Ga and Ge in different crystallographic sites leads to a more Ge-rich composition; instead, in La₂AlGe₆ (La₂Al_{1.6}Ge_{5.4}) a partial substitution of Ge by Al atoms is reflected in a more Ge-poor composition. In these cases the total number of atoms per unit cell is coincident with the stoichiometric model, but a more correct general formula should be $R_2M_{1-x}Ge_{6+x}$, where x could be positive or negative. For $R = Y$, $M = Ga$ both possibilities are realized; 20 in fact, two compounds have been reported with these elements, a Ge-rich phase $(Y_2Ga_{0.34}Ge_{6.66}, 0.0572, x = 0.66)$ and a G[e-p](#page-13-0)oor one $(Y_2Ga_3Ge_4, mS36, x = -2)$.

On the basis of these data and considering that no transition elements of group 12 had been taken into account up to now, we decided to explore the existence and crystal structure of an analogous series of R_2MG_6 compounds where $M = Zn$. Here, we present the synthesis and structural characterization of the new R₂Zn_{1−x}Ge₆ series (R = La–Nd, Sm, Gd–Ho), enriching the 2:1:6 family with a new structure type (found for $R = Dy$). The role of Zn deficiency in governing structural changes will be particularly discussed. A general group−subgroup relation scheme based on vacancy ordering is also proposed to rationalize the crystal structures inside this family and extended to $R_2Zn_3Ge_6$ compounds. Moreover, results of electronic structure calculations on La_2ZnGe_6 will be presented in order to complete the characterization of these polar intermetallics from the chemical bonding point of view.

2. EXPERIMENTAL SECTION

2.1. Synthesis, Microstructure, and Phase Analysis. Samples of about 0.8 g with $R_{22.2}Zn_{11.1}Ge_{66.7}$ (R = La–Nd, Sm, Gd–Tm) nominal compositions were prepared by direct synthesis from the pure

Table 2. Crystallographic Data for $R_2Zn_{1-x}Ge_6$ (R = La, Ce, Nd, Gd, Tb, Dy) Single Crystals, and Experimental Details of the Structural Determination

empirical formula		$Ce2Zn1-xGe6$			$Tb_2Zn_{1-x}Ge_6$	
	$La2Zn1-xGe6$		$Nd_2Zn_{1-x}Ge_6$	$Gd_{2}Zn_{1-x}Ge_{6}$		$Dy_2Zn_{1-x}Ge_6$
code	crystal I	crystal II	crystal III	crystal IV	crystal V	crystal VI
x (EDXS)	0.011	0.051	0.15	0.33	0.39	0.43
x (structural model)	0.063(6)	0.089(9)	0.156(5)	0.364(6)	0.437(6)	0.50
structure type	$Ce_2(Ga_{0.1}Ge_{0.9})_7$	$Ce_2(Ga_{0.1}Ge_{0.9})_7$	$Ce_2(Ga_{0.1}Ge_{0.9})_7$	$Ce_2(Ga_{0.1}Ge_{0.9})_7$	$Ce_2(Ga_{0.1}Ge_{0.9})_7$	$Dy_2Zn_{1x}Ge_6$
cryst syst	orthorhombic	orthorhombic	orthorhombic	orthorhombic	orthorhombic	monoclinic
space group	Cmce (No. 64)	Cmce (No. 64)	Cmce (No. 64)	Cmce (No. 64)	Cmce (No. 64)	$P2_1/m$ (No. 11)
$M_{\rm w}$ [g/mol]	774.64	775.18	779.18	791.63	790.32	793.22
Pearson symbol, Z	$oS72 - 0.50, 8$	$oS72 - 0.71, 8$	$oS72 - 1.25, 8$	$oS72 - 2.91, 8$	$oS72 - 3.50, 8$	$mP36 - 2.00, 4$
$a \hat{A}$	8.7294(9)	8.6498(12)	8.5437(10)	8.3559(10)	8.3041(5)	7.9613(3)
$b \lceil \mathbf{A} \rceil$	8.2841(8)	8.2578(11)	8.1765(9)	8.0377(10)	8.0053(5)	8.2480(4)
$c [\text{Å}]$	21.483(2)	21.340(3)	21.175(2)	20.876(3)	20.7898(13)	10.5309(5)
β [deg]						100.861(1)
$V\left[{\rm \AA}^3\right]$	1553.6(3)	1524.3(4)	1479.3(3)	1402.1(3)	1382.04(15)	679.12(5)
calcd density $[g/cm^3]$	6.659	6.756	6.997	7.500	7.870	7.758
abs coeff (μ) , mm ⁻¹	36.53	37.686	40.358	45.993	49.168	49.481
unique reflns	1021	1307	982	930	1122	2195
reflns $I > 2\sigma(I)$	788 $(R_{\text{sigma}} = 0.0272)$	1133 $(R_{\text{sigma}} = 0.0235)$	904 $(R_{\text{sigma}} = 0.0135)$	509 $(R_{\text{sigma}} = 0.0313)$	813 $(R_{\text{sigma}} = 0.0125)$	1795 $(R_{\text{sigma}} = 0.0196)$
data/parameters	1021/51	1307/50	982/51	930/51	1122/51	2195/100
GOF on F^2 (S)	1.13	1.15	1.29	1.00	1.16	0.98
final R indices $[I >$ $2\sigma(I)$	$R_1 = 0.0283$; $wR_2 = 0.0736$	$R_1 = 0.0537$ $wR_2 = 0.1585$	$R_1 = 0.0220$ $wR_2 = 0.0464$	$R_1 = 0.0280$; $wR_2 = 0.0555$	$R_1 = 0.0242$ $wR_2 = 0.0496$	$R_1 = 0.0268$; $wR_2 = 0.0683$
R indices (all data)	$R_1 = 0.0371$; $wR_2 = 0.0790$	$R_1 = 0.0576$ $wR_2 = 0.1634$	$R_1 = 0.0236$ $wR_2 = 0.0470$	$R_1 = 0.0639$; $wR_2 = 0.0678$	$R_1 = 0.0364$ $wR_2 = 0.0543$	$R_1 = 0.0361$ $wR_2 = 0.0742$
$\Delta\rho_{\text{fin}}$ (max/min) [e/Å ³]	$2.64/-1.91$	$7.98/-4.91$	$1.77/-1.19$	$2.53/-2.53$	$2.03/-3.24$	$3.96/-3.08$

components (rare-earth metals and zinc were supplied by Newmet Koch, Waltham Abbey, England, and germanium by MaTecK, Jülich, Germany; nominal purities of all metals > 99.9 mass %). The stoichiometric amounts of the pure metals were enclosed in an arcsealed Ta crucible with the aim to avoid Zn losses due to evaporation. The crucible was then closed in an evacuated quartz vial to prevent oxidation and placed in a resistance furnace where the following thermal cycle was applied: (1) heating (10 °C/min) up to $T = 950$ °C; (2) cooling down (about 0.5 $\mathrm{C/min}$) to 350 C . During the thermal cycle, a continuous rotation, at a speed of 100 rpm, was applied to the vial. Samples were subsequently quenched in cold water. The obtained alloys are very brittle. No tantalum contamination of the samples was observed.

Samples were embedded in a phenolic hot mounting resin with carbon filler. Smooth alloys surfaces suitable for the microscopic examinations were obtained by means of SiC papers and diamond pastes with particle size decreasing from 6 to 1 μ m. After each polishing step samples were ultrasonically cleaned for a few minutes in a petroleum ether bath. Microstructure observation and qualitative/ quantitative analysis were performed by a scanning electron microscope (SEM) EVO 40 (Carl Zeiss SMT Ltd., Cambridge, England) provided with a Pentafet Link energy-dispersive X-ray spectroscopy (EDXS) system controlled by the package Inca Energy (Oxford Instruments, Analytical Ltd., Bucks, U.K.). Cobalt standard was used for calibration.

2.2. X-ray Diffraction Measurements. Single crystals of good quality and size were extracted from the mechanically fragmented alloys and selected with the aid of a light optical microscope (Leica DM4000 M, Leica Microsystems Wetzlar GmbH, Welzlar, Germany) operated in the dark field mode. The crystals under analysis, exhibiting metallic luster, were mounted on glass fibers using quick-drying glue. Intensity data have been collected at ambient conditions (295 K) on a four-circle Bruker Kappa APEXII CCD area detector diffractometer equipped with graphite-monochromatized Mo K α radiation (λ = 0.71073 Å). The instrument was operated in the ω scan mode. Intensity data were collected over the reciprocal space up to \sim 30° in θ with exposures of 20−30 s per frame. Semiempirical absorption corrections based on equivalents were applied to all data by the SADABS software.²³ X-ray diffraction on powder samples was performed by means of a Philips X'Pert MPD diffractometer (Cu $K\alpha$ radiation, step [m](#page-13-0)ode of scanning) in order to ensure crystal structures of the studied phases.

Selected crystallographic data and structure refinement parameters for the six studied phases are listed in Table 2. The crystal structure solution, requiring a detailed description, is discussed in section 3.1.

Details on structure refinement can be also found in the Supporting Information in the form of a CIF file. The [C](#page-1-0)IF file has also been deposited with Fachinformationszentrum Karlsruhe, 76344 Eggenstein-Leopoldshafen, Germany: depository numbers C[SD-428090](#page-12-0) (La₂Zn_{1-x}Ge₆-crystal I), CSD-428091 (Ce₂Zn_{1-x}Ge₆-crystal II), CSD-428092 (Nd₂Zn_{1-x}Ge₆-crystal III), CSD-428093 (Gd₂Zn_{1-x}Ge₆-crystal IV), CSD-428680 (Tb₂Zn_{1-x}Ge₆-crystal V), and CSD-428094 $(Dy_2Zn_{1-x}Ge_6-crystal VI)$. The powder patterns generated from the single-crystal models correspond well to the observed powder diffraction patterns.

2.3. Vacancy Ordering Modeling Basing on Symmetry **Principle.** The $ToposPro²⁴$ software was applied with the goal to deduce structural models related to an aristotype (parent structure) by selected criteria satisfying [the](#page-13-0) symmetry principle.¹⁵ In particular, we were interested in generating structural models related to an aristotype through a vacancy ordering involving a specific o[rbi](#page-12-0)t of it (to obtain the wanted composition) and resulting in a desired local topology. To achieve this result several steps were needed:

- (1) generation of all possible subgroups of the aristotype of a certain order,
- (2) selection of a subset where the considered original orbit is split in two (a splitting into more orbits would contradict the symmetry principle),
- (3) removal of one-half of the generated sites, corresponding to vacancies, and

(4) search for the structures containing the desired fragment. This final step was done using the original ToposPro algorithm of searching for a finite fragment in an infinite periodic net.

A step by step description of this procedure applied to the 2:1:6 family of structures is available in the Supporting Information.

2.4. Electronic Structure Calculations. The electronic band structure of La₂Zn_{1−x}Ge₆ (x = 0, idealized model corresponding to the stoichiometry 2:1:6) was calculated b[y](#page-12-0) [means](#page-12-0) [of](#page-12-0) [the](#page-12-0) [self-con](#page-12-0)sistent, tight-binding, linear-muffin-tin-orbital method using the Stuttgart TB-LMTO-ASA 4.7 program²⁵ in the local density (LDA) and the atomicspheres approximations (ASA) in the framework of the DFT method. Two empty spheres we[re](#page-13-0) introduced to satisfy the LMTO volume criterion (less than 10%; their positions were deduced by the automatic procedure implemented in the code). The average ASA radii for the constituents were as follows: La = 2.13 Å, Ge = $1.42-1.52$ Å, $Zn = 1.49$ Å, empty spheres of ca. 1.04 Å both.

The basis sets included 6s, (6p), 5d, and 4f orbitals for La, 4s, 4p, and 3d orbitals for Zn, and 4s, 4p, and (4d) orbitals for Ge with orbitals in parentheses being downfolded.²⁶

The k-space integrations were done using an improved tetrahedron method²⁷ with 365 irreducible k-points [m](#page-13-0)esh in the first Brillouin zone. The energies and crystal orbital Hamilton populations (COHP) conver[gen](#page-13-0)ce with respect to the number of k points was checked in all calculations. The density of states (DOS) , $(COHP)$ curves,²⁶ and integrated COHP values (iCOHPs) were also calculated in order to evaluate orbital interactions. Plots of DOS and COHP curv[es](#page-13-0) were generated using wxDragon.²¹

3. RESULTS AND DI[SC](#page-13-0)USSION

3.1. Crystal Structure Determination of R₂Zn_{1−x}Ge₆ (La, Ce, Nd, Gd, Tb, Dy) Germanides. Cell indexation was straightforward for crystals with $R = La$, Ce, Nd, and Tb (crystals I−III and V), giving an orthorhombic C-centered cell $(h + k = 2n$ reflections were observed). The analysis of systematic extinctions suggested as possible space groups Cc2e (No. 41) and Cmce (No. 64). The same, almost complete, structural model was obtained in a few iteration cycles by applying the charge-flipping algorithm implemented in JANA2006. ²⁹ In this model the rare-earth atoms are situated in a 16g general site, while the other six positions were accidentall[y a](#page-13-0)ssigned to the lighter elements: in fact, the very similar X-ray scattering powers of Ge and Zn (which are only 2e[−] different) make it difficult to distinguish between them. In any case the δ 672 Pearson symbol is associated with this model. The final structure was then obtained by distributing Ge and Zn among the appropriate sites, taking into account both the measured compositions and previous knowledge on similar compounds, such as $\text{La}_2\text{MgGe}_6^{\frac{1}{4}}$ and $\text{Dy}_2\text{PdGe}_6^{\frac{18}{4}}$ At this point it became clear that the La-, Ce-, Nd-, and Tb-containing compounds are isopointal with [t](#page-12-0)he $Ce_2(Ga_{0.1}Ge_{0.9})_7$ prototype.

Further structure refinements were carried out by full-matrix least-squares methods on $|F^2|$ using the SHELX programs³⁰ as implemented in WinGX.³¹ The anisotropically refined R_2ZnGe_6 models showed acceptable residuals and flat difference Fo[ur](#page-13-0)ier maps. An unusual value [of](#page-13-0) Zn 8f site anisotropic displacement parameter (ADP) was found for $Nd₂ZnGe₆$: for this reason its occupancy factor (SOF) was left to vary in further cycles, converging to ca. 0.85 and leading to even lower residuals and homogeneous ADP values for all species. At this point SOFs of all species were checked for deficiency, obtaining nevertheless values very close to unity. The same procedure was applied to the Tb analogue, converging to ca. 0.56 and to La and Ce compounds, giving a less pronounced Zn deficiency along with better residuals.

reconstructed precession foto

Figure 1. Observed intensity profiles for the hk0 zone demonstrating the presence of weak super-reflections. The reciprocal lattice corresponding to the C-centered monoclinic cell is shown in green; the reciprocal lattice of the monoclinic superstructure is shown in white; for clarity only some super-reflections are asterisked. The 3D image of the area marked in blue, highlighting the difference of peaks intensities, is also shown (left).

$La2AlGe6-mS36$		La:8i	Ge1:8j			Ge2:4i		Ge3:4i		Ge4:4i		Ge5:4i	Al:4i	
C12/m1	0.085 0.248 0.336		0.278		\boldsymbol{m}		\boldsymbol{m}			m		m		m
					0.07			0.986		0.146		0.140		0.300
k ₂				0.213		Ω	1/2		Ω		1/2		1/2	
$1/4$, $1/4$, 0			0.113		0.112		0.113		0.564		0.580		0.195	
Dy_2ZnGe_6-mP36	Dyl:4f	Dy2:4f	Ge1:4f	Ge2:4f	Ge3:2e	Ge4:2e	Ge5:2e	Ge6:2e	Ge7:2e	Ge8:2e	Ge $9:2e$	Ge10:2e	Zn2:2e	Zn1:2e
$P_1 2_1/m_1$					\boldsymbol{m}	m	\boldsymbol{m}							
(calculated)	0.335	0.835	0.538	0.038	0.320	0.820	0.237	0.736	0.396	0.896	0.390	0.890	0.550	0.050
	0.498	0.998	0.463	0.963	1/4	3/4	3/4	1/4	1/4	3/4	3/4	1/4	3/4	1/4
	0.336	0.336	0.113	0.113	0.112	0.112	0.113	0.113	0.564	0.564	0.580	0.580	0.195	0.195
$\rm Dy_2Zn_{1-x}Ge_6-mP34$	Dyl:4f	Dy2:4f	Ge1:4f	Ge2:4f	Ge3:2e	Ge4:2 e	Ge5:2e	Ge6:2e	Ge7:2e	Ge8:2e	Ge $9:2e$	Ge $10:2e$	\mathbb{Z}/\mathbb{Z} n2:2e	Zn1:2e
$P_1 2_1/m_1$					\boldsymbol{m}	m	m	\mathfrak{m}	\boldsymbol{m}	\boldsymbol{m}	\boldsymbol{m}	\boldsymbol{m}	m	\boldsymbol{m}
(refined)	0.334	0.834	0.529	0.029	0.322	0.791	0.270	0.734	0.400	0.892	0.393	0.891	0.550	0.050
	0.498	0.002	0.491	0.960	1/4	3/4	3/4	1/4	1/4	3/4	3/4	1/4	3/4	1/4
	0.336	0.336	0.119	0.115	0.115	0.122	0.122	0.114	0.580	0.562	0.582	0.585	0.203	0.201

Figure 2. Group−subgroup relation in the *Bärnighausen* formalism for the mS36-La₂AlGe₆ and mP36-2-Dy₂Zn_{1−x}Ge₆ structural models. The type and order of the symmetry reduction and the evolution of the atomic parameters are shown.

The structure solution of $Gd_2Zn_{1-x}Ge_6$ (crystal IV) deserves a separate description. Despite the very good quality of the crystal, the indexation of the ca. 650 reflections selected from the complete collected data set was not unambiguous. In fact, the difference vectors and fast Fourier transform algorithms inside $APEX2^{23}$ suggested two different unit cells with very close score values: a C-orthorhombic cell ($a = 8.02$ Å, $b = 8.33$ [Å,](#page-13-0) $c = 20.83$ Å, $V = 1393$ Å³) and a *P*-monoclinic cell ($a = 8.04$ Å, $b = 8.36$ Å, $c = 10.64$ Å, $\beta = 100.91^{\circ}$, $V = 703$ Å³). After refinement both cells give very similar deviation histograms (see the Supporting Information), so that further integration was done for both cells independently. The analysis of the reflection [conditions with](#page-12-0) $XP\mathbb{R}P^{23}$ showed that the monoclinic choice was not compatible with any space group; instead, the orthorhombic one leads to t[he](#page-13-0) Cmce space group. The structural model was refined analogously to crystals I−III and V, giving for the Zn site a SOF ≈ 0.64 .

In the case of the Dy crystal (*crystal VI*) a routine analysis of the obtained data set suggested a C-centered monoclinic cell (a = 7.96 Å, $b = 8.25$ Å, $c = 10.53$ Å, $\beta = 100.9^{\circ}$). No systematic absences associated with symmetry elements were found, so structure solution was attempted in the $C2/m$ space group, giving an adequate structural model (JANA2006) with excellent residuals (SHELX). This mS36 model is isopointal with the monoclinic $La₂AlGe₆$ prototype, showing a pronounced Zn deficiency (site $4i$, SOF = 0.49). Occupancy factors values close to $1/2$, $1/3$, $1/4$, etc., are often warning signs of a more chemically sound superstructure, where the atom distribution is better modeled by a higher number of sites, resulting from symmetry reduction.^{4−6,10} This is the reason why a more careful analysis of the reciprocal diffraction lattice was performed. In fact, [nume](#page-12-0)rous weak super-reflections were clearly discerned (as an example, see the reconstructed precession photo in Figure 1).

Considering these weak super-reflections, indexation results in a primitive monoclinic cell with the same lattice parameters. A new model was found by JANA2006 in the $P2_1/m$ (No. 11) space group, containing 13 crystallographic positions: for analogy with other 2:1:6 compounds 2 of them were assigned to Dy, 10 to Ge, and 1 to Zn atoms. Nonetheless, one additional prominent peak maximum at 0.45, 1/4, 0.80 was found on the difference Fourier map. This peak was associated with an additional Zn position, but considering the distances to the closest neighbors the SOFs of Zn sites were left to vary. As the sum of SOFs for them was close to unity, this condition was constrained to hold up in further cycles of refinement (obtaining a SOFs ratio of $0.82(Zn1):0.18(Zn2)$). In the final mP36-2 model containing 14 positions, all atoms were refined anisotropically except for the Zn1−Zn2 couple; their ADPs were constrained to be identical. The refinement converged at $R1 = 0.0268$, $wR2 = 0.0683$, and GOF = 0.98 complemented by a flat difference Fourier map. The goodness of the accepted model is also highlighted by the less pronounced anisotropic displacement parameters for Ge atoms closest to Zn positions and by a more homogeneous distribution of all ADPs.

Frequently, a superstructure requiring an enlargement of the unit cell is klassengleiche group−subgroup related to the structural model assumed initially, which is why such a relation

was looked for between the $mS36$ -La₂AlGe₆ and $mP34$ -Dy₂Zn_{1–x}Ge₆ structural models. From the *Bärnighausen* chart shown in Figure 2 it can be noted that refined atomic coordinates of the major part of observed atom positions $(Dy_2Zn_{1-x}Ge_6-mP34)$ $(Dy_2Zn_{1-x}Ge_6-mP34)$ fit very well with those obtained from corresponding sites splitting $(Dy_2Zn_{1-x}Ge_6-mP36)$; the 1/2 1/2 0 translation vector vanishes, leaving more degrees of freedom for a shift of Ge species and causes the formation of two independent Zn sites (having different SOFs in the final model). These features can be interpreted in terms of a vacancy ordering phenomenon, which will be discussed in more detail in the following paragraphs.

3.2. Microstructure, Phase Analysis, and Crystal Structure Description of the R_2Zn_1 _{-x}Ge₆ Phases. Phases detected in ternary samples of nominal composition $R_{22.2}M_{11.1}Ge_{66.7}$ are listed in the Supporting Information, together with their measured compositions and lattice parameters. All examined alloys are [multiphase: for all rare](#page-12-0)earth metals, except for Er and Tm, the main phase is a ternary compound where the ratio between elements approaches the 2:1:6 stoichiometry. Common secondary phases are Ge $(R =$ La, Sm, Gd, Dy–Tm), RGe_{2−x} (R = La–Nd, Sm, Tm), $R_2Zn_3Ge_6$ (R = La–Pr, Sm, Gd–Ho), $R_4Zn_5Ge_6$ (R = Er, Tm), and RZn_xGe_2 (R = Tb–Er). This last series of novel compounds is currently under investigation in our research group. A new ternary compound was also detected for Sm of composition ∼Sm₂₇Zn₆Ge₆₇. Selected microphotographs of the characterized samples are also shown in the Supporting Information. Along the 2:1:6 series, the measured Zn content smoothly decreases on increasing the R atomic num[ber, passing](#page-12-0) [from 11.0 at](#page-12-0)om % (for La) to 5.7 atom % (for Ho); the general formula $R_2Zn_{1-x}Ge_6$ conveniently accounts for this feature.

The X-ray diffraction powder patterns can be satisfactorily interpreted assuming the $R_2Zn_{1-x}Ge_6$ compounds belonging to any of the three structural models reported in the literature (see Introduction), whose crystal spaces are indeed characterized by the same distribution of the rare-earth metal atoms and most of [the lighter c](#page-0-0)onstituents. The small differences between these models are hardly distinguishable in the theoretical powder patterns and not visible at all in the experimental patterns of multiphase samples, where strong peak overlapping occurs.

For these reasons single-crystal X-ray diffraction was performed on several samples along the series $(R = La, Ce,$ Nd, Gd, Tb, Dy) with the aim to find the correct structural model(s) and shed more light on the Zn deficiency. To our knowledge, such behavior was not previously detected in the R2MGe6 family; instead, it was observed for other R−Zn−Ge series of compounds, especially for heavy rare-earth metals.³²

Considering the single crystals (see section 3.1) and powder X-ray diffraction analysis results together with the beha[vio](#page-13-0)r regularities along the R series it was con[clud](#page-2-0)ed that the orthorhombic structure $(oS72-Ce_2(Ga_{0.1}Ge_{0.9})_7)$ is realized for R = La−Nd, Sm, Gd−Tb and the monoclinic one (mP34- $Dy_2Zn_{1-x}Ge_6$) for the Dy analogue. Unfortunately, it was not possible to isolate a good quality $Ho_2Zn_{1-x}Ge_6$ single crystal; nevertheless, we are inclined to believe that the latter is also monoclinic since the structure changed passing from Tb to Dy.

The established structural models (see Table 3) support the Zn deficiency (and its trend within the series) suggested by the EDXS characterization. In fact, in both the ort[ho](#page-4-0)rhombic and the monoclinic compounds the SOFs of the Zn sites are <1, leading to a smooth decrease of the Zn content along the R series. This trend is plotted in Figure 3, where only the x values

Figure 3. Normalized cell volumes (both from single-crystal and powder XRD data) and deficiency (x) of R₂Zn_{1−x}Ge₆ compounds as a function of the R^{3+} ionic radius.

obtained from single crystals were considered. In the same figure the cell volume linearly decreasing along the series is also shown; in order to compare the different structures, the monoclinic cell volume was doubled (in this way the same number of atoms was taken into account).

From the interatomic distances analysis of all the compounds (see Table 4 and the Supporting Information) it is possible to highlight the presence of two types of covalently bonded Ge fragments, [sh](#page-6-0)own in [Figure 4: 2D zigzag chain](#page-12-0)s formed by twobonded (2b-) Ge atoms and 3D corrugated layers formed by three-bonded (3b-) Ge ato[ms](#page-7-0). Within these fragments the Ge− Ge distances range from ca. 2.46 to 2.63 Å and are not strongly affected by the lanthanide contraction. These motifs, common to the orthorhombic and monoclinic structures, are joined by Zn−Ge bonds to form a framework whose channels are filled by the bigger R atoms. Each Zn atom is connected to five Ge atoms (dotted lines in Figure 4) with distances comparable to their atomic radii sum: the shortest of them corresponds to the links between Zn and the 2D [ge](#page-7-0)rmanium zigzag chains. Passing from La to Tb this contact regularly shrinks, as a consequence of both the lanthanide contraction and the increasing Zn deficiency effects. A non-negligible contribution of the Zn deficiency can be revealed by comparing the trend of Zn−Ge distances in the analogous framework in $R_2Zn_3Ge_6$ compounds (R = La–Nd).¹¹ In the monoclinic Dy₂Zn_{1-x}Ge₆ compound (Figure 4b) the Ge covalent fragments are linked in a slightly different mann[er,](#page-12-0) and the Zn linkers occupy two distinct sites characte[riz](#page-7-0)ed by very different SOFs: the Zn−Ge link distance for the higher SOF Zn atoms is on the order of atomic sum radii; instead, that for the remaining Zn species (with very low SOF) is physically unreasonable.

It is appropriate to underline here that also the germanium 3D covalent fragments undergo a significant change when examining the whole series of compounds. These fragments are infinite, corrugated layers composed of interconnected squares, and they can be viewed also as distorted α -Po motifs (see Introduction). Their distortion degree, which can be qualitatively evaluated by the Ge–Ge–Ge obtuse angle (α) [indicated in F](#page-0-0)igure 4a, decreases along with the zinc content, so the less distortion found in the orthorhombic compounds

occurs for the Tb analogue, where $\alpha \approx 100^{\circ}$ and SOF(Zn) = 0.56. For the monoclinic compound the distortion locally depends on the SOF value of the capping Zn atom, being more pronounced for the Zn highly occupied 2e site (see insert in Figure 4b). A similar distortion was observed for $\text{RAl}_{1-x}\text{Ge}_2^5$ and $\text{RFe}_{1-x}\text{Ge}_2^6$ compounds in planar Ge networks capped by Al or F[e](#page-7-0).

An ideal α -P[o](#page-12-0) layer formed by Ge atoms (with all Ge–Ge– Ge solid angles equal to 90°) exists in the binary compound TmGe₃, where these layers are directly linked to Ge–Ge zigzag chains by Ge–Ge contacts.⁹

From previous considerations it is clear that the Zn content is a key factor for the stru[ctu](#page-12-0)ral changes along this series.

3.3. R_2MCe_6 Family in Terms of Vacancy Ordering. It often happens that very similar crystal structures (also with related metric conditions) are group−subgroup related: it is not the case of δ 672-Ce₂(Ga_{0.1}Ge_{0.9})₇ and *mS*36-La₂AlGe₆. An alternative relation was looked for through a common supergroup, but no aristotype was found for which the Wyckoff sites split generates the two structural models under study. Nevertheless, they were described by Zhao et al. 34 as vacancy variants of the orthorhombic $SmNiGe₃$ type. Adopting this point of view we decided to start from this a[ris](#page-13-0)totype and reduce its symmetry, considering vacancies as a part of the symmetry criteria. Results are summarized in Figure 5 in the form of a *Bärnighausen* tree (the corresponding evolutions of atomic parameters are provided in the Supporting [In](#page-8-0)formation). All three oS72, mS36, and mP36-2 structures find their own place inside this two-branched tree. The δ 5[72 stays on the](#page-12-0) [orth](#page-12-0)orhombic branch, resulting from two successive k2 reduction steps. Referring to the atomic species, the original orbit of the Ni atoms splits in two subsets: one is occupied by Zn atoms, and the other remains vacant.

The monoclinic branch starts from the *mS36* model, resulting after two successive reduction steps, of t2 and k2 type. Also, in this case the original 4i Ni site splits into two 4i sites, one of which is vacant. At this point, the two 2:1:6 models situated at the same level of hierarchy could be called "isomers". Their different vacancy (empty circles) distribution is shown in Figure 6a, where the trace of the aristotype unit cell is evidenced in red. In terms of constituting structural fragments, one can [o](#page-9-0)bserve that for both isomers one-half of the bridging atoms entails a similar distortion of the 3D corrugated Ge layers (see Figure 6b).

The *oS72* and *mS36* models can be the starting points of a further klassenglei[ch](#page-9-0)e reduction, leading to 4:1:12 isomers characterized by an even smaller number of bridging atoms. The *mP*36-2 model found for the Dy₂Zn_{1-x}Ge₆ phase is one of them on the monoclinic branch. The symmetry reduction between mS36 and mP36-2 was already described in section 3.1 while discussing how the correct structural model was discerned; generalized schemes like this are helpful in solv[ing](#page-2-0) new structures, providing a finite number of models to test.¹⁵

In order to check if other 2:1:6 isomers may exist, deriving from the $SmNiGe₃$ aristotype and characterized by the sa[me](#page-12-0) symmetry criteria, the ToposPro software was applied using the batch of algorithms described in section 2.3 and in the Supporting Information. Only the subgroups of fourth order were considered. At the end of this proced[ure](#page-2-0) only the two [isomers already describ](#page-12-0)ed were found. The same procedure could be applied to find all 4:1:12 isomers starting from each of the 2:1:6 models; however, no orthorhombic 4:1:12 isomers were found characterized by the same local topology as the idealized monoclinic Dy₂Zn_{1-x}Ge₆ ($x = 0.5$, only one Zn site fully occupied, composition Dy_4ZnGe_{12}).

At this point it is clear that the vacancy ordering criterion has been a successful approach to find a general scheme including all of the structures found. On the other hand, the structural and chemical role of vacancy phenomena has been described for other germanides^{4,35–37} and different classes of compounds, such as intermetallic clathrates, $38,39$ γ -brasses, $40,41$ and superconducting oxides.¹⁴

 $mP34-Dy_2Zn_{1-x}Ge_6$

Figure 4. Representation of the crystal structures of (a) $R_2Zn_{1-x}Ge_6$ (oS72) and (b) $Dy_2Zn_{1-x}Ge_6$ (mP34) as composed of Zn–Ge networks sandwiched by R atoms (filled in green). Within this network the homocontacts Ge−Ge are shown in red; the heterocontacts Zn−Ge are black dotted lines. To highlight the different distortion degree of the 3b-Ge corrugated layers in these two structures, their projections along the c direction are shown in the left part of the figure (empty spheres represent Zn atoms with the smallest SOF, "+" indicates capping Zn atoms situated under the plane of image, remaining Zn atoms are located above it). The different spatial distribution/connection of the 2b-Ge "zigzag" chains with the 3b-Ge corrugated layers through the Zn linkers is shown to the right.

The proposed scheme based on vacancy ordering is complementary to the geometrical description of the same family of compounds in terms of linear intergrowth of topologically related fragments (of BaAl₄, AlB₂, and α -Po structure types). In particular, our approach describes also the compositional change of the $BaAl₄$ -type slab, which is $RX₄$ for SmNiGe₃, R $\Box X_3$ for the 2:1:6 isomers, and R $\Box_2 X_2$ for Dy_4ZnGe_{12} (R = bigger atom, X = smaller atom(s)). Thus, it allows us to relate structures belonging to different homological series.^{42,43} Nevertheless, the linear intergrowth representation of the SmNiGe₃ and the 2:1:6 derivatives is useful to visualize the s[ubtle](#page-13-0) differences between these structures (see Supporting Information).

3.4. $R_2Zn_3Ge_6$ Series of Compounds. Co[mpounds of](#page-12-0) formula $R_2Zn_3Ge_6$ and crystal structure $oS44$ -La₂Zn₃Ge₆, known from the literature for R = La-Nd,¹¹ were found as secondary phases in many samples synthesized in this work (see the Supporting Information). Therefore, [it](#page-12-0) was possible to

confirm their existence and crystal structure for some light rareearth metals and to extend the series to R = Sm, Gd−Ho. The powder diffraction patterns of our samples can be indexed assuming the $oS44$ -La₂Zn₃Ge₆ structure model for these heavy rare-earth 2:3:6 analogues.

The calculated cell volumes are shown in Figure 7 as a function of the R^{3+} radius, together with literature data: a linear decreasing trend is obtained, in agreement with the lan[th](#page-9-0)anide contraction phenomenon.

The $oS44$ - $R_2Zn_3Ge_6$ structures were described by Salvador et al.¹¹ as composed from PbO-like ZnGe layers and $ZnGe₄$ layers, with R atoms embedded within. Here, we propose an al[ter](#page-12-0)native description from the linear intergrowth point of view, discerning three types of intergrown 2D fragments (Figure 8) of BaAl₄, Ba \Box Al₃, and α -Po topology (their compositions are RZn_2Ge_2 , RZn_2Ge_2 , and Ge_2 , respectively). This des[cri](#page-10-0)ption highlights the similarity between the $R_2Zn_3Ge_6$ and the $R_2Zn_{1-x}Ge_6$ families, particularly the presence of similar

 $La₂ZnGe₆$

Figure 5. *Bärnighausen* tree relating the SmNiGe₃ aristotype and its orthorhombic and monoclinic vacancy variants. The type and indexes of the symmetry reductions are given.

3b-Ge-based corrugated layers capped by Zn atoms. Also, the interatomic distances within these fragments are very close for La representatives of the two series. For these reasons the vacancy ordering structural criterion was applied and proved to be valid also for the 2:3:6 series. The vacancy-free aristotype was found using the PSEUDO algorithm on the Bilbao server⁴⁴ after adding another Zn species in the appropriate position (4c site at 0, 0.348, 1/4). The obtained structure really exists, and [it](#page-13-0) has only the $tI24-ScNi₂Si₃$ representative. Thus, the $R_2Zn_3\Box Ge_6$ structure can be obtained from this aristotype reducing its symmetry in two steps: a translationengleiche (t2) decentering followed by a second-order klassengleiche transformation (k2), as represented in Figure 8 (left branch) in the form of a Bärnighausen tree. The corresponding evolution of atomic parameters is provided in the Sup[po](#page-10-0)rting Information. It can be noted that this reduction does not contradict the symmetry principle (i.e., the number [of Zn sites after splitting](#page-12-0) is minimal, only two). At this point, all 2:3:6 isomers can be generated from the $ScNi₂Si₃$ aristotype, applying the same ToposPro algorithms described for the 2:1:6 compounds. Also, in this case only two isomers were obtained: the already discussed $R_2Zn_3\Box Ge_6$ (oS44, space group Cmcm) and the hypothetical " $R_2Zn_3\Box Ge_6$ " (tI88, space group I4₁/amd). The latter is represented in the right branch of Figure 8, and no real representatives of it are known to date. The linear intergrowth repr[es](#page-10-0)entation of $ScNi₂Si₃$ and its 2:3:6 derivatives is shown in

the Supporting Information. The 2:3:6 isomers can become the starting points of further symmetry reductions (and vacancy con[centration increase\),](#page-12-0) leading to hypothetical 4:5:12 stoichiometries.

On the basis of this scheme one cannot exclude that even in the $R_2Zn_3Ge_6$ series vacancy ordering phenomena may exist, giving a general formula $R_2 Zn_{3-x}Ge_6$ ($R_4 Zn_5Ge_{12}$ for $x = 0.5$) and leading to crystal structures different from $oS44$ for some heavy rare-earth metals. Some experimental hints of this scenario already exist.

- (1) The $R_2Zn_3Ge_6$ series extends up to $R = Ho$ as the $R_2Zn_{1-x}Ge_6$ series.
- (2) The EDXS measured compositions of $R_2Zn_3Ge_6$ show deviations from the ideal stoichiometry. The entity of this deviation and its trend along the R series (see the Supporting Information) are compatible with the $R_2Zn_{3-x}Ge_6$ hypothetical formula. In fact, the fraction [of vacancies with respect t](#page-12-0)o the overall number of atoms in the unit cell is smaller than for $R_2Zn_{1-x}Ge_6$. For example, the measured composition for $R = Ho(24.8)$ atom % Zn; 56.2 atom % Ge) is closer to the hypothetical $Ho_4Zn_5Ge_{12}$ formula than to the $Ho₂Zn₃Ge₆ stoichiometry.$

X-ray single-crystal measurements would be necessary to confirm/discard this hypothesis. Selected structure models to

Figure 6. (a) Vacancy (empty circles) distribution in La₂ZnGe₆ (δ 672) and La₂AlGe₆ (δ 636) with respect to the SmNiGe₃ aristotype unit cell evidenced in red; (b) distortion of the 3b-Ge corrugated layer in La₂Al□Ge₆ compared with that in SmNiGe₃.

Figure 7. Cell volumes of $R_2Zn_3Ge_6$ compounds as a function of the R^{3+} ionic radius ((O) from ref 11; (\bullet) this work).

test can be obtained extending the scheme of Figure 8 with further symmetry reduction based on a higher degree of vacancy ordering.

The $La_2Zn_3Ge_6$ compound was studied by Salvador [et](#page-10-0) al.¹¹ also from the chemical bonding point of view. With the goal of comparing the chemistry of the polar 2:1:6 and 2:3[:6](#page-12-0) compounds, electronic structure calculations were performed on the $La₂ZnGe₆$ idealized model, and results are discussed in the next paragraph.

3.5. Electronic Structure Calculations for $La₂ZnGe₆$. The bonding in $R_2Zn_{1-x}Ge_6$ ($x = 0$, idealized models) can be initially addressed by the Zintl−Klemm concept.45,46 Following this idea, the calculated valence electron concentration on Ge atoms, being $\langle 8 \text{ (VEC(Ge)} = 5.3)$, suggests t[he p](#page-13-0)resence of polyanionic network(s). The average number of Ge−Ge homocontacts is $8 - \text{VEC}(Ge) = 2.7$, in agreement with the presence of two types of Ge fragments, with two and three homocontacts. Taking into account their ratio in the structure, the simplified ionic formula $(R^{3+})_2(Zn^{2+})(2b\text{-}Ge^2)_2(3b\text{-}Ge^-)_4$ is obtained.

With the aim of investigating the chemical bonding within the 2:1:6 series, the electronic structure of La_2ZnGe_6 was

Figure 8. *Bärnighausen* tree relating the ScNi₂Si₃ aristotype and its orthorhombic and tetragonal vacancy variants. The type and indexes of the symmetry reductions are given.

computed by the TB-LMTO-ASA software. The La analogue was chosen for two reasons: it has no partially filled 4f orbitals, and its composition is very close to the idealized 2:1:6 stoichiometry.

The total and projected densities of states (DOS) of $La₂ZnGe₆$ are shown in Figure 9.

Figure 9. Total and projected DOS for La_2ZnGe_6 (E_F is set at 0 eV).

The DOS curve is characterized by a small number of states at the Fermi level, indicating a metallic character. Nevertheless, a minimum of the DOS (pseudogap) lies just below E_F .

The wide prominent peak from 3 to 5 eV in the conduction band is mainly due to the empty f La states.

The valence band (VB) of the DOS plot can be divided into two distinct regions: up to −6 eV and from −6 eV to E_F . The lower region is dominated by the filled d^{10} states of Zn atoms (prominent sharp peak between −9 and −8 eV). This feature was already observed for the structurally and chemically similar $R_{2}Zn_{3}Ge_{6}^{2}$ and $Ca_{2}Zn_{3}Sn_{6}^{47}$ compounds, where these states are regarded as "pseudo core states", so that Zn behaves as a "pseudo [m](#page-12-0)ain group el[em](#page-13-0)ent". This is confirmed by the distribution of s and p states of Zn, spread over the region from −6 eV to EF, where they overlap with s and p states of Ge. These features suggest a s−p-bonded $[ZnGe₆]^{δ-}$ network, following the scenario proposed by Häussermann et al.⁴⁸ for a large number of binary and ternary polar intermetallics, including germanides.

A significant contribution of d states of La is observed just below the Fermi level, indicating that the La atoms do not transfer completely their valence electrons to the polyanionic network. These valence d states are hybridized with p states of Ge, suggesting strong La−Ge interactions, supported by the reciprocal arrangements and interatomic distances between

Figure 10. Crystal orbital Hamilton populations (−COHP) per bond for La2ZnGe6 from LMTO calculations: (a) Ge−Ge interactions; (b) Zn−Ge interactions; (c) La−Ge interactions.

these atoms in the crystal structure (see the presence of $GeLa₆$ trigonal prisms within the AlB_2 -type slabs). The partial DOS curves relevant for this discussion are shown in the Supporting Information.

Further indications on bonding interactions [and their](#page-12-0) [strength can](#page-12-0) be taken from the COHP curves (shown in Figure 10) and their integrated values (−iCOHP, listed in Table 4).

The Ge−Ge and Zn−Ge interactions change their character from [bo](#page-6-0)nding to antibonding type just below the Fermi level: similar features have been often interpreted in the literature as a qualitative indication that an ideal "electron tuning" would be achieved for a somewhat more electron poor model.^{49,50} In fact, this is coherent with the real La₂Zn_{1−x}Ge₆ model, showing a small Zn deficiency, which indeed increases along t[he se](#page-13-0)ries. In the Ge−Ge COHP curves (Figure 10a) two different behaviors can be distinguished. The curve corresponding to the Ge−Ge (2b-) forming zigzag chains shows a small antibonding region below E_F (around −7 eV) corresponding to π^* states. An analogous interpretation was proposed for topologically identical zigzag Ge chains in CaGe.⁵¹ More pronounced π interactions were observed for Ge−Ge dumbbells in different binary and ternary germanides, such as AE_7Ge_6 $(AE = Ba, Sr)^{52}$
La Mg Ge 8 Gd Zn Ge 53 and Gd MgGe 54 $\rm La_4Mg_5Ge_{67}^8\,Gd_4Zn_5Ge_{67}^{53}$ and $\rm Gd_2MgGe_2.$

The COHP curve of Ge−Ge (3b-) interaction states [is](#page-13-0) spread over [a](#page-12-0) larger ener[gy](#page-13-0) region (starting [fr](#page-13-0)om about −12.5 eV) and changes its character from bonding to antibonding type only close to E_F .

The character of La−Ge interactions (Figure 10c) becomes of the antibonding type well above E_F , further evidence of the incomplete polarization of La atoms.

The Ge−Ge bonds are associated with the highest −iCOHP values, which are typical for Ge-Ge covalent interactions.^{8,52} These values range from 1.94 to 2.33 eV/bond inside the zigzag chains and from 1.91 to 2.75 eV/bond for the corrugated lay[e](#page-12-0)[rs.](#page-13-0)

In each type of Ge-based fragment the −iCOHP follow the trend of interatomic distances. Within the $[ZnGe_6]^{\delta-}$ covalent network, somewhat weaker interactions are found between Zn and Ge, the corresponding −iCOHP varying from 1.27 and 1.44 eV/bond. Finally, the numerous La−Ge bonds are associated with lower −iCOHP values, around 1 eV/bond. Other contacts within the first coodination sphere are irrelevant.

The chemical bonding scenario presented above suggests to describe the $R_2Zn_{1-x}Ge_6$ compounds as near Zintl phases, similar to the closely related $R_2 Zn_3Ge_6$ compounds.²

4. CONCLUSIONS

The nine new $R_2Zn_{1-x}Ge_6$ compounds (R = La–Nd, Sm, Gd– Ho) were presented in this work, with particular emphasis on their crystal structure peculiarities and regularities in the framework of the $~\sim R_2MGe_6$ family (M = transition metal + Mg, Al, Ga). The studied series of intermetallics shows two interesting and peculiar characteristics.

- (1) A Zn deficiency regularly increasing with the atomic number of the lanthanide, confirmed both by EDXS measurements and by accurate single-crystal XRD studies. Nevertheless, other Zn-containing intermetallics show a similar deficiency tendency.
- (2) A structural change from the orthorhombic structure $oS72-Ce_2(Ga_{0,1}Ge_{0,9})$ ₇ (for R = La–Nd, Sm, Gd, Tb) to the new monoclinic structure mP34-Dy₂Zn_{1-x}Ge₆ (x \approx 0.5, for $R = Dy$, Ho), which represents an ordered superstructure of the $La₂AlGe₆$ prototype.

These two structural models are closely related, being characterized by the same Ge-based infinite motifs, namely, 2D zigzag chains and 3D corrugated layers, linked by Zn atoms in slightly different manners. Nonetheless, the heavy R atoms distribution is identical, miming a strong pseudosymmetry

which hampers the correct structural model deduction. This could be the reason why the structure of several R_2MG_6 compounds, initially reported as $oS18-Ce_2CuGe_6$, was subsequently redetermined as the four times bigger $oS72$ - $Ce_2(Ga_{0.1}Ge_{0.9})$. From this perspective we think that the structure of many other 2:1:6 phases would need a revision.

Besides the orthorhombic to monoclinic structural change some regularities can be traced along the $R_2Zn_{1-x}Ge_6$ series, depending on the R nature and/or on the Zn content:

- (1) the normalized cell volume linearly decreases, reflecting the lanthanide contraction trend, and
- (2) the distortion degree of the 3D corrugated layers decreases, due to the always smaller number of capping Zn atoms.

The role of Zn deficiency in governing the structures of the studied compounds motivated us to look for a generalization scheme including vacancy ordering phenomena as a key principle. This goal was achieved within group theory with the help of group−subgroup relations in the Bärnighausen formalism. Moreover, this procedure was automated in the ToposPro software package in order to guarantee its completeness.

The resulting scheme is a two-branched Bärnighausen tree originating from the $SmNiGe₃$ aristotype via subsequent reduction steps accompanied by vacancy ordering. Within this tree, the 2:1:6 compounds with oS72 and mS36 structures can be viewed as "isomers" located each on a different branch, both obtained after two reduction steps of the second order but characterized by different vacancy distributions. Growing longer the monoclinic branch from the mS36 model, the mP34 structure (corresponding to the compound $Dy_2Zn_{1-x}Ge_6 \approx$ Dy_4ZnGe_{12}) is obtained via one k2 reduction step along with further vacancy ordering.

The same approach was applied to the $R_2Zn_3Ge_6$ family, enriched during this work with the new Sm and Gd−Ho analogues. A similar two-branched *Bärnighausen* tree was proposed, originating from the $ScNi₂Si₃$ aristotype: two 2:3:6 "isomers" have been particularly derived, having the oS44 (reported for the studied $R_2 Zn_3Ge_6$ compounds) and tI88 (hypothetic) structures. Efforts to obtain the first representative of the latter are in progress.

Finally, structural studies were complemented with electronic calculations performed on the idealized model $La₂ZnGe₆$, confirming for this series of compounds the existence of a $[ZnGe₆]^{ö–}$ polyanionic network counterbalanced by La ions. Therefore, they can be defined as polar intermetallics with near Zintl behavior.

The numerous interesting results presented here trigger several further studies, including the exploration of novel germanides characterized by similar covalent fragments and the revision/expansion of the R_2MG_6 family of compounds along with quantum chemical analysis in real space according to the quantum theory of atoms in molecules $(QTAIM),^{55}$ aiming to a deeper insight into chemical bonding.

■ ASSOCIATED CONTENT

6 Supporting Information

X-ray crystallographic files in CIF format; SEM/EDXS and XRPD characterization results; interatomic distances; deviation histograms for $Gd_2Zn_{1-x}Ge_6$ single-crystal data; backscattered electron images of alloys surfaces; evolutions of atomic parameters in the *Bärnighausen* formalism between the

SmNiGe₃ aristotype and La₂Zn \Box Ge₆ and between the SmNiGe₃ aristotype and Dy₂Zn_{1−x}Ge₆; evolutions of atomic parameters in the *Bärnighausen* formalism between the ScNi₂Ge₃ aristotype and La₂Zn₃ \Box Ge₆; studied structures in terms of linear intergrowth representation; partial DOS curves for $La₂ZnGe₆$; description of the algorithm of the vacancy ordering modeling in the 2:1:6 family starting from the $SmNiGe₃$ aristotype using ToposPro (the material necessary to reproduce the process is also provided in a separate archive). This material is available free of charge via the Internet at http://pubs.acs.org.

■ [AUTHOR INF](http://pubs.acs.org)ORMATION

Corresponding Author

*Phone: +39-0103536159. Fax: +39-0103536163. E-mail: pavlo.solokha@unige.it.

Notes

[The authors declare no](mailto:pavlo.solokha@unige.it) competing financial interest.

■ ACKNOWLEDGMENTS

This research was funded by the University of Genoa within PRA 2013 projects. D.M.P. and V.A.B. thank the Russian government (grant No. 14.B25.31.0005) for support. The authors thank Sergio Fiorito, an undergraduate student, for his contribution to this research in an early stage.

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■ NOTE ADDED AFTER ASAP PUBLICATION

This paper was published ASAP on February 10, 2015. Tables 1 and 2 were updated. The revised paper was reposted on February 18, 2015.